DG211B/212B

Improved Quad CMOS Analog Switches

Features

- ±22-V Supply Voltage Rating
- TTL and CMOS Compatible Logic
- Low On-Resistance—$r_{DS(on)}$: 50 Ω
- Low Leakage—$I_{D(on)}$: 20 pA
- Single Supply Operation Possible
- Extended Temperature Range
- Fast Switching—t_{ON}: 120 ns
- Low Charge Injection—Q: 1 pC

Benefits

- Wide Analog Signal Range
- Simple Logic Interface
- Higher Accuracy
- Minimum Transients
- Reduced Power Consumption
- Superior to DG211/212

Applications

- Industrial Instrumentation
- Test Equipment
- Communications Systems
- Disk Drives
- Computer Peripherals
- Portable Instruments
- Sample-and-Hold Circuits

Description

The DG211B/212B analog switches are highly improved versions of the industry-standard DG211/212. These devices are fabricated in Siliconix' proprietary silicon gate CMOS process, resulting in lower on-resistance, lower leakage, higher speed, and lower power consumption.

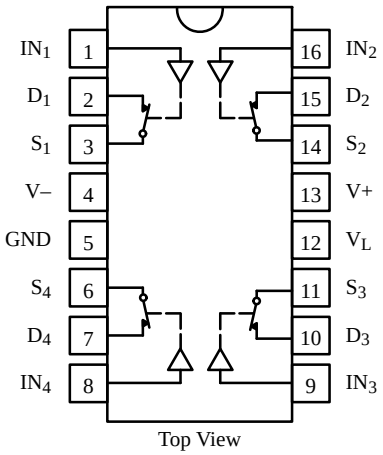
These quad single-pole single-throw switches are designed for a wide variety of applications in telecommunications, instrumentation, process control, computer peripherals, etc. An improved charge injection compensation design minimizes switching transients. The DG211B and DG212B can handle up to ±22 V, and have an improved continuous current rating of 30 mA. An epitaxial layer prevents latchup.

All devices feature true bi-directional performance in the on condition, and will block signals to the supply levels in the off condition.

The DG211B is a normally closed switch and the DG212B is a normally open switch. (See Truth Table.)

Functional Block Diagram and Pin Configuration

Dual-In-Line and SOIC



Top View

Truth Table

Logic	DG211B	DG212B
0	ON	OFF
1	OFF	ON

Logic "0" ≤ 0.8 V
Logic "1" ≥ 2.4 V

Switches Shown for Logic "0" Input

Ordering Information

Temp Range	Package	Part Number
–40 to 85°C	16-Pin Plastic DIP	DG211BDJ
		DG212BDJ
	16-Pin Narrow SOIC	DG211BDY
		DG212BDY

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70040.

Absolute Maximum Ratings

Voltages Referenced to V–

V+ . . . . . 44 V

GND . . . . . 25 V

Digital Inputs[a] V_S, V_D . . . . . (V–) –2 V to (V+) +2 V or 30 mA, whichever occurs first

Current, Any Terminal . . . . . 30 mA

Peak Current, S or D
(Pulsed at 1 ms, 10% duty cycle max) . . . . . 100 mA

Storage Temperature . . . . . –65 to 125°C

Power Dissipation (Package)[b]

16-Pin Plastic DIP[c] . . . . . 470 mW

16-Pin Narrow SOIC[d] . . . . . 640 mW

Notes:
a. Signals on S_X, D_X, or IN_X exceeding V+ or V– will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
b. All leads welded or soldered to PC Board.
c. Derate 6.5 mW/°C above 75°C
d. Derate 7.6 mW/°C above 75°C

Specifications

Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 15 V, V– = –15 V V_L = 5 V, V_{IN} = 2.4 V, 0.8 V[e]	Temp[a]	D Suffix –40 to 85°C Min[c]	Typ[b]	Max[c]	Unit
Analog Switch							
Analog Signal Range[d]	V_{ANALOG}		Full	−15		15	V
Drain-Source On-Resistance	$r_{DS(on)}$	V_D = ±10 V, I_S = 1 mA	Room Full		45	85 100	Ω
$r_{DS(on)}$ Match	$\Delta r_{DS(on)}$		Room		2		
Source Off Leakage Current	$I_{S(off)}$	V_S = ±14 V, V_D = ∓14 V	Room Full	−0.5 −5	±0.01	0.5 5	nA
Drain Off Leakage Current	$I_{D(off)}$	V_D = ±14 V, V_S = ∓14 V	Room Full	−0.5 −5	±0.01	0.5 5	
Drain On Leakage Current	$I_{D(on)}$	V_S = V_D = 14 V	Room Full	−0.5 −10	±0.02	0.5 10	
Digital Control							
Input Voltage High	V_{INH}		Full	2.4			V
Input Voltage Low	V_{INL}		Full			0.8	
Input Current	I_{INH} or I_{INL}	V_{INH} or V_{INL}	Full	–1		1	µA
Input Capacitance	C_{IN}		Room		5		pF
Dynamic Characteristics							
Turn-On Time	t_{ON}	V_S = 2 V See Figure 2	Room		85	150	ns
Turn-Off Time	t_{OFF}		Room		77	120	
Charge Injection	Q	C_L = 1000 pF, V_g= 0 V, R_g = 0 Ω	Room		1		pC
Source-Off Capacitance	$C_{S(off)}$	V_S = 0 V, f = 1 MHz	Room		5		pF
Drain-Off Capacitance	$C_{D(off)}$		Room		5		
Channel On Capacitance	$C_{D(on)}$	V_D = V_S = 0 V, f = 1 MHz	Room		16		
Off Isolation	OIRR	C_L = 15 pF, R_L = 50 Ω V_S = 1 V_{RMS}, f = 100 kHz	Room		90		dB
Channel-to-Channel Crosstalk	X_{TALK}		Room		95		

Specifications

Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 15 V, V– = –15 V V_L = 5 V, V_{IN} = 2.4 V, 0.8 V[e]	Temp[a]	D Suffix –40 to 85°C Min[c]	Typ[b]	Max[c]	Unit
Power Supply							
Positive Supply Current	I+	V_{IN} = 0 or 5 V	Room Full			10 50	µA
Negative Supply Current	I–		Room Full	–10 –50			
Logic Supply Current	I_L		Room Full			10 50	
Power Supply Range for Continuous Operation	V_{OP}		Full	±4		±22	V

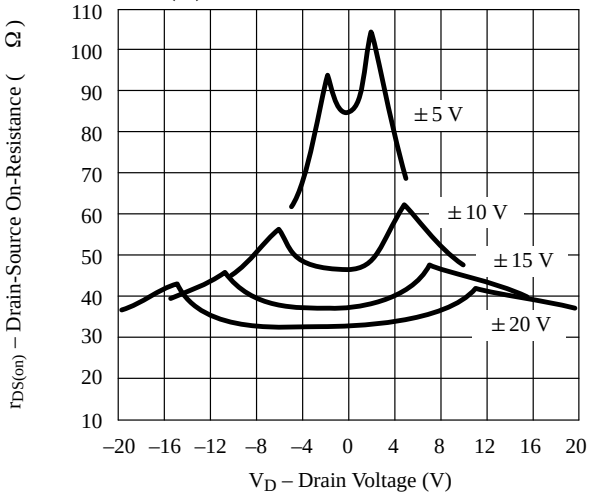
Specifications for Single Supply

Parameter	Symbol	Test Conditions Unless Otherwise Specified V+ = 12 V, V– = 0 V V_L = 5 V, V_{IN} = 2.4 V, 0.8 V[e]	Temp[a]	D Suffix –40 to 85°C Min[c]	Typ[b]	Max[c]	Unit
Analog Switch							
Analog Signal Range[d]	V_{ANALOG}		Full	0		12	V
Drain-Source On-Resistance	$r_{DS(on)}$	V_D = 3 V, 8 V, I_S = 1 mA	Room Full		90	160 200	Ω
Dynamic Characteristics							
Turn-On Time	t_{ON}	V_S = 8 V See Figure 2	Room			300	ns
Turn-Off Time	t_{OFF}		Room			200	
Charge Injection	Q	C_L = 1 nF, V_{gen}= 6 V, R_{gen} = 0 Ω	Room		4		pC
Power Supply							
Positive Supply Current	I+	V_{IN} = 0 or 5 V	Room Full			10 50	µA
Negative Supply Current	I–		Room Full	–10 –50			
Logic Supply Current	I_L		Room Full			10 50	
Power Supply Range for Continuous Operation	V_{OP}		Full	+4		+44	V

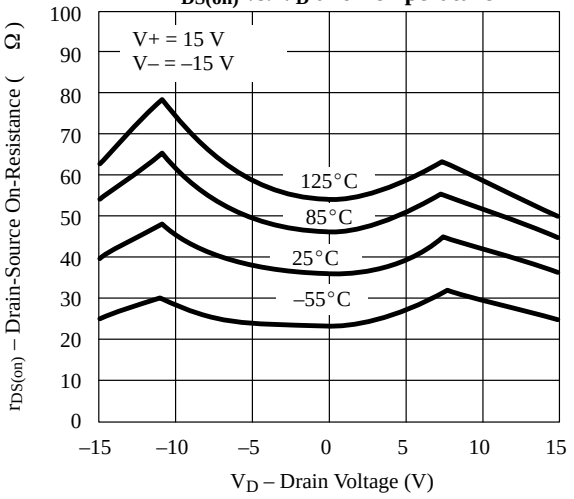
Notes:
a. Room = 25°C, Full = as determined by the operating temperature suffix.
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
d. Guaranteed by design, not subject to production test.
e. V_{IN} = input voltage to perform proper function.

Typical Characteristics

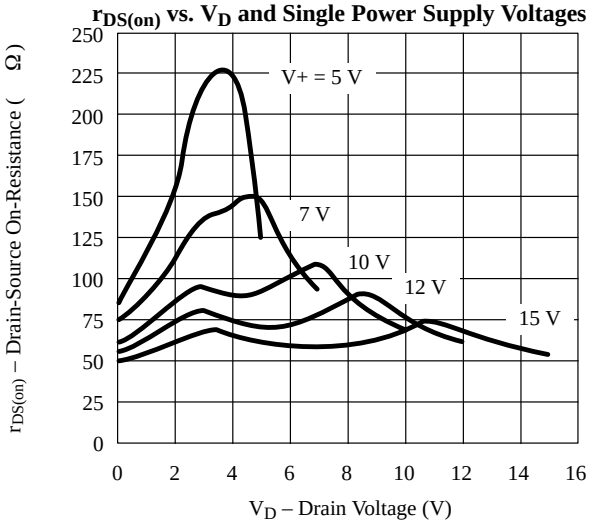
$r_{DS(on)}$ vs. V_D and Power Supply Voltages



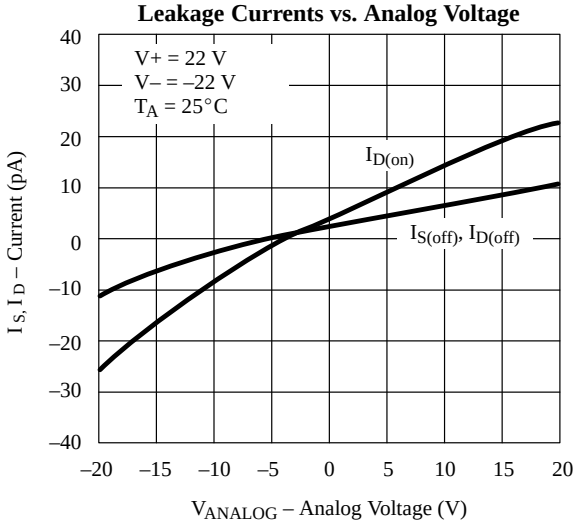
$r_{DS(on)}$ vs. V_D and Temperature



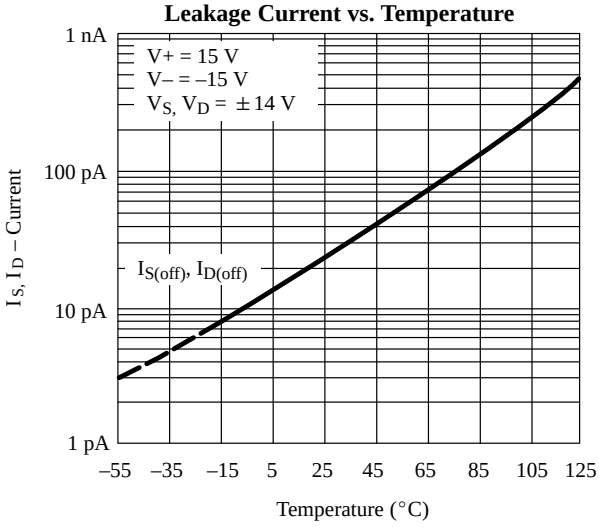
$r_{DS(on)}$ vs. V_D and Single Power Supply Voltages



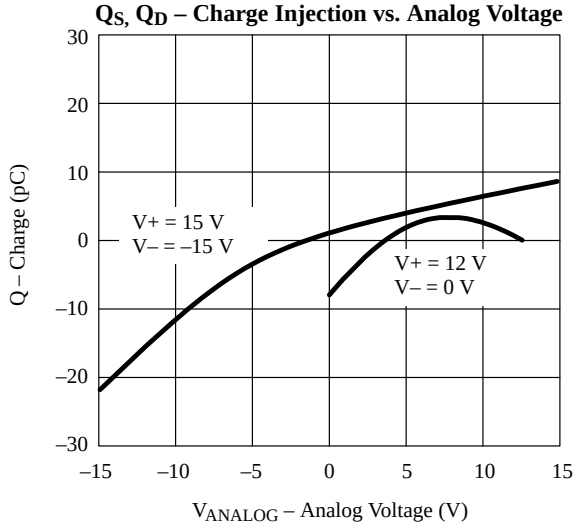
Leakage Currents vs. Analog Voltage



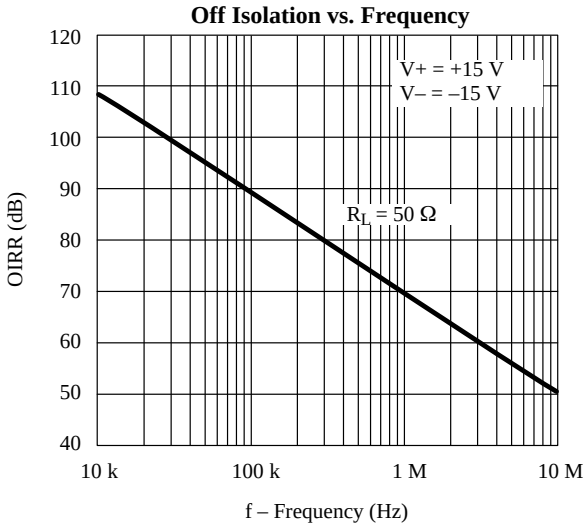
Leakage Current vs. Temperature



Q_S, Q_D – Charge Injection vs. Analog Voltage



Typical Characteristics (Cont'd)



Schematic Diagram (Typical Channel)

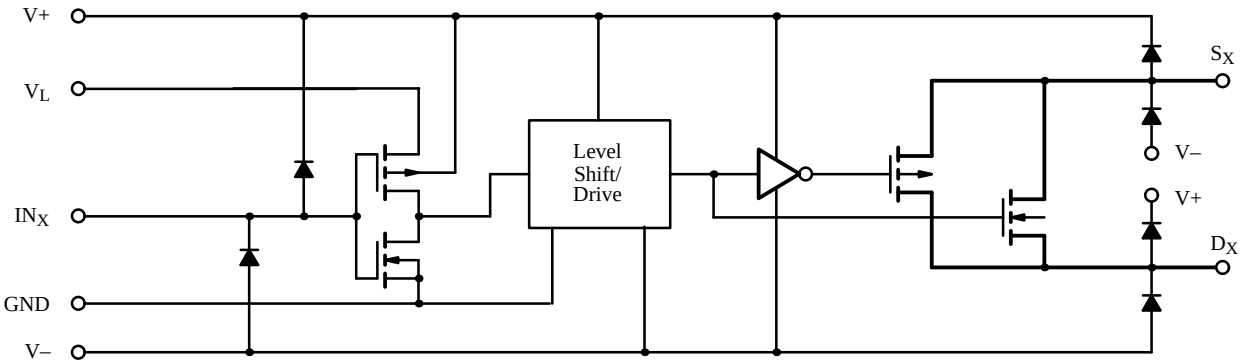


Figure 1.

Test Circuits

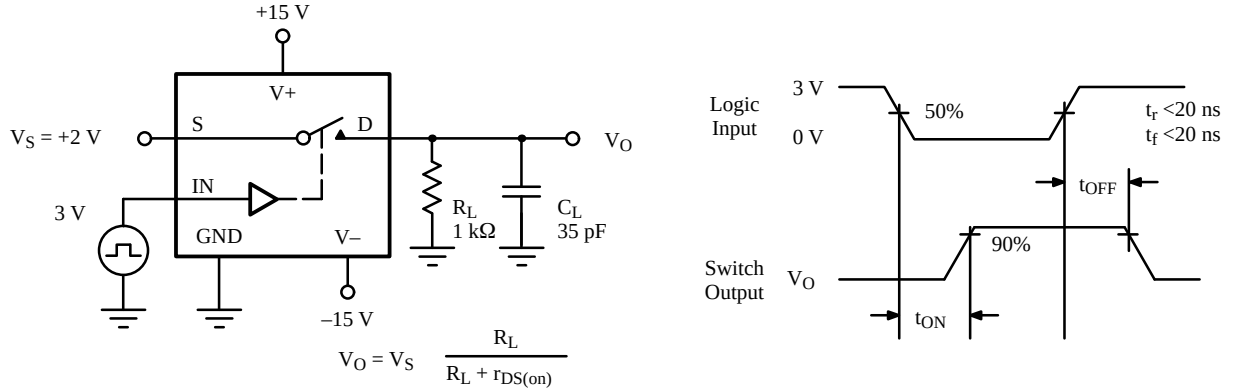


Figure 2. Switching Time

Test Circuits (Cont'd)

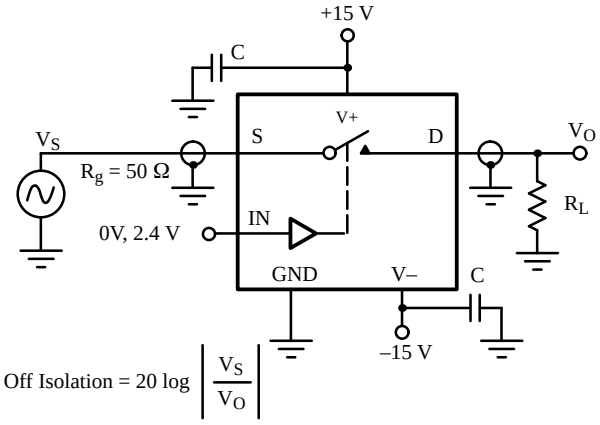


Figure 3. Off Isolation

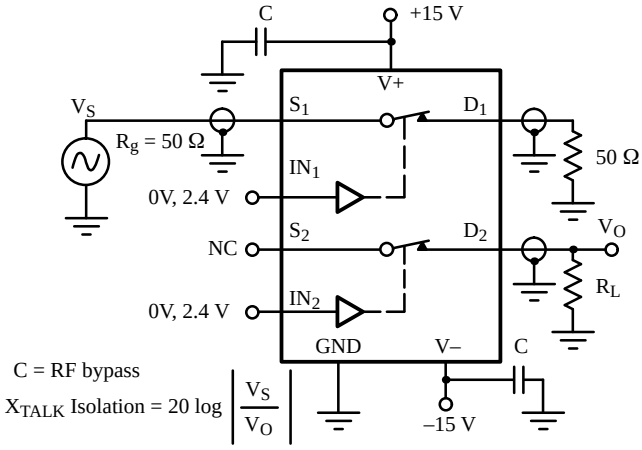
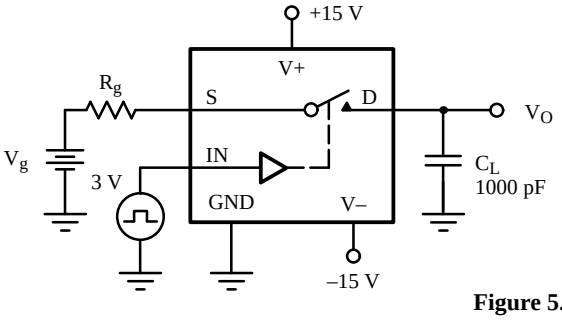
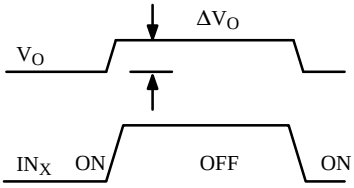


Figure 4. Channel-to-Channel Crosstalk

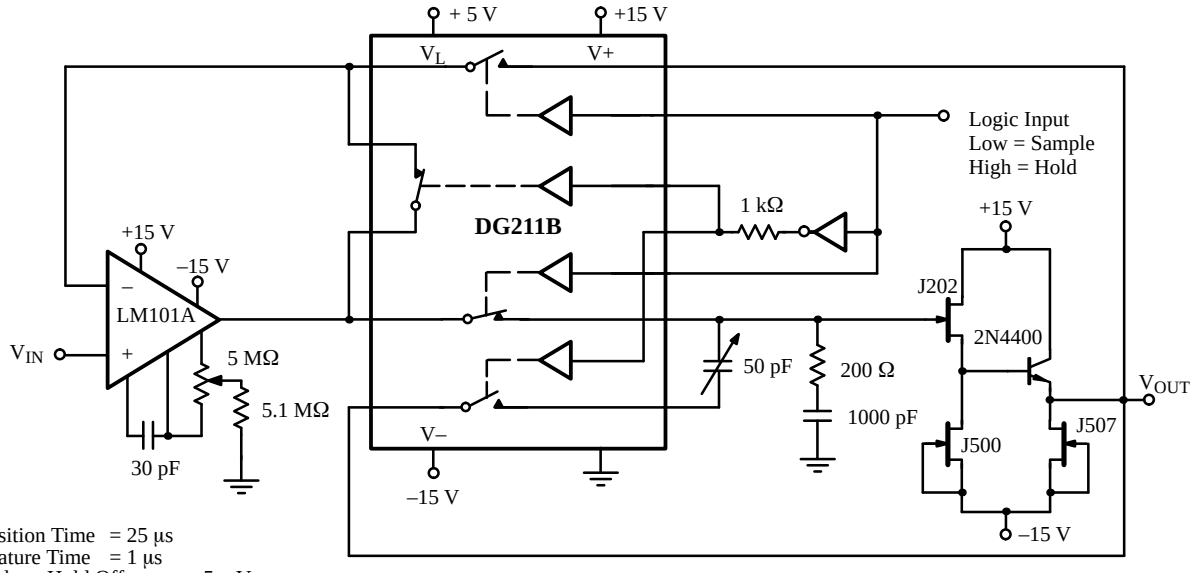




ΔV_O = measured voltage error due to charge injection
The charge injection in coulombs is $Q = C_L \times \Delta V_O$

Figure 5. Charge Injection

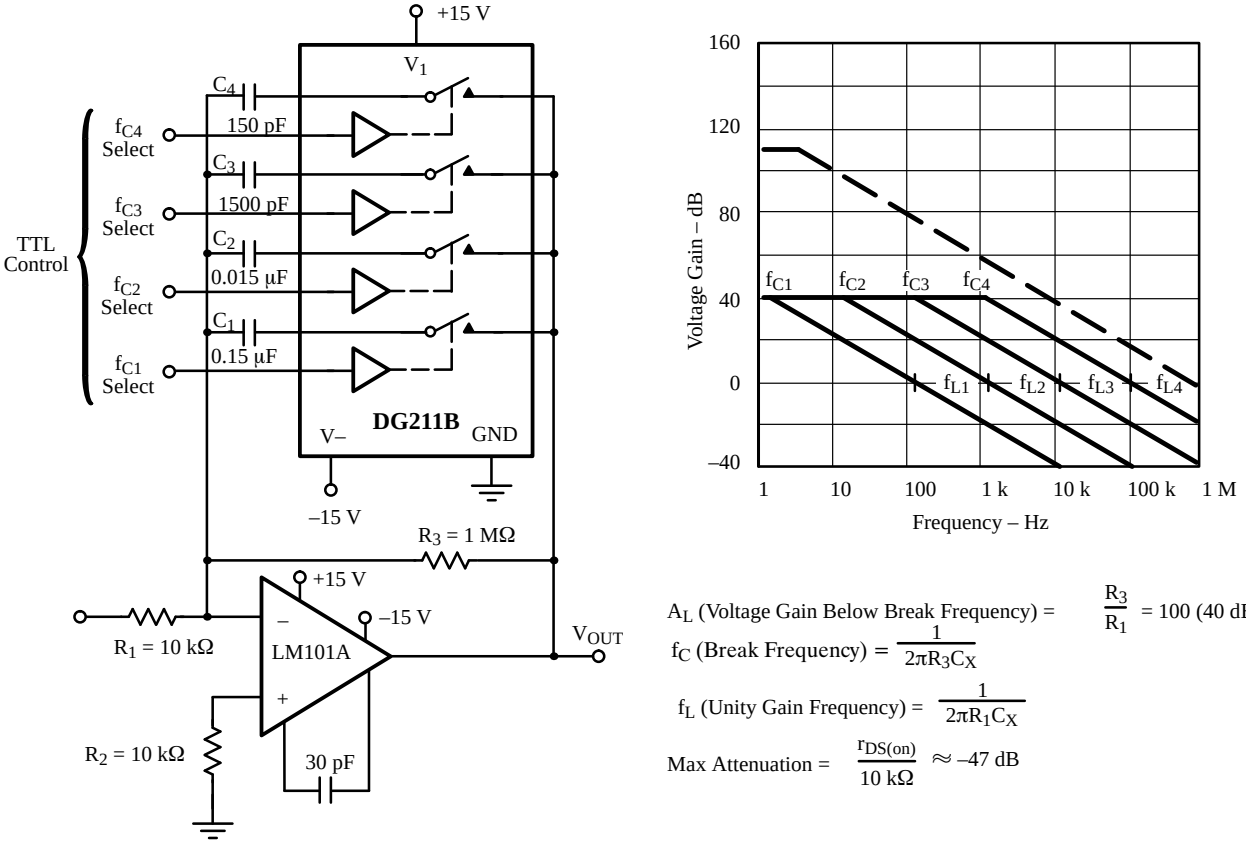
Applications



Aquisition Time = 25 µs
Aperature Time = 1 µs
Sample to Hold Offset = 5 mV
Droop Rate = 5 mV/s

Figure 6. Sample-and-Hold

Applications (Cont'd)



A_L (Voltage Gain Below Break Frequency) = $\frac{R_3}{R_1}$ = 100 (40 dI

f_C (Break Frequency) = $\frac{1}{2\pi R_3 C_X}$

f_L (Unity Gain Frequency) = $\frac{1}{2\pi R_1 C_X}$

Max Attenuation = $\frac{r_{DS(on)}}{10\ k\Omega} \approx -47$ dB

Figure 7. Active Low Pass Filter with Digitally Selected Break Frequency

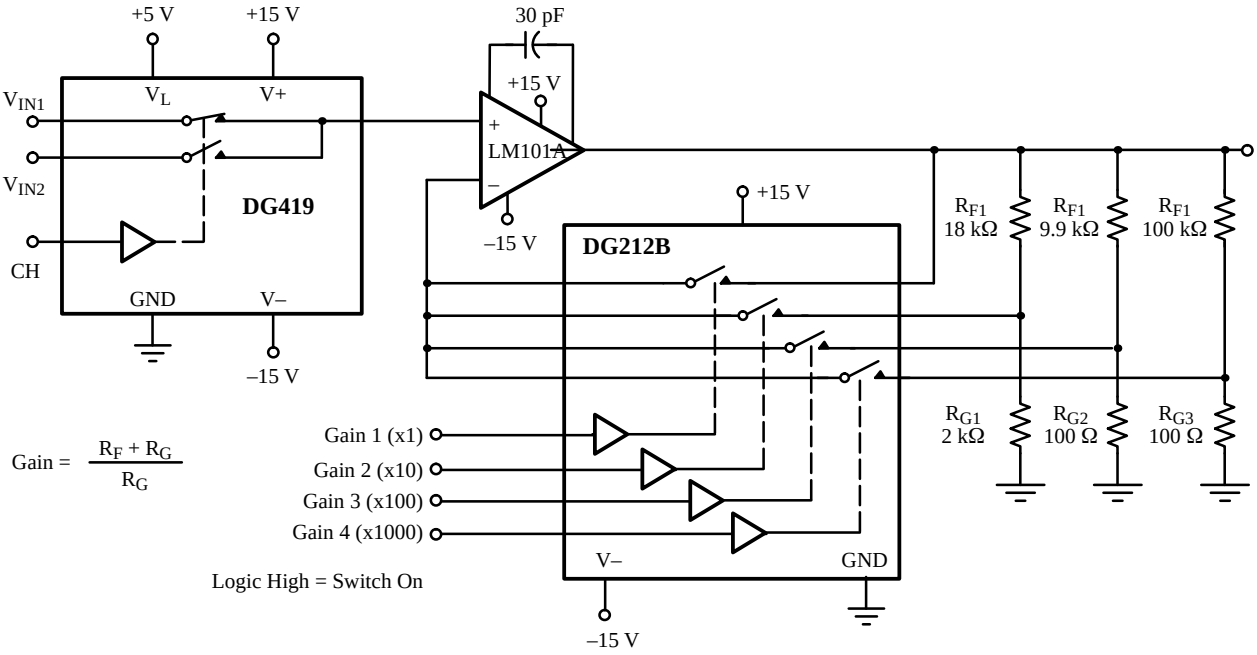


Figure 8. A Precision Amplifier with Digitally Programable Input and Gains